



New Product

Si5935DC
Vishay Siliconix

Dual P-Channel 1.8-V (G-S) MOSFET

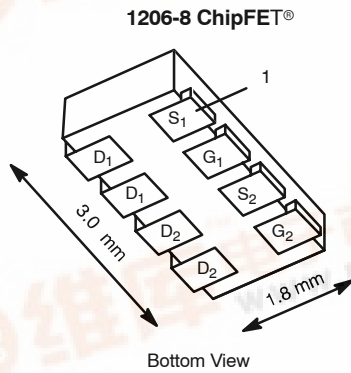
PRODUCT SUMMARY		
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)
-20	0.086 @ V _{GS} = -4.5 V	-4.1
	0.121 @ V _{GS} = -2.5 V	-3.4
	0.171 @ V _{GS} = -1.8 V	-2.9

FEATURES

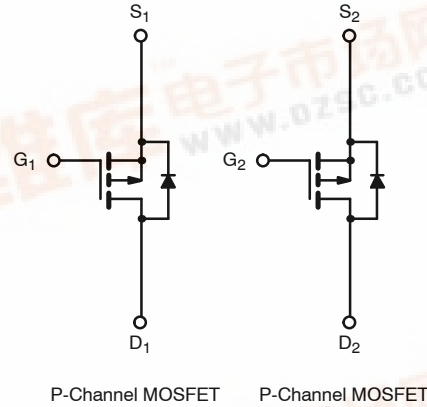
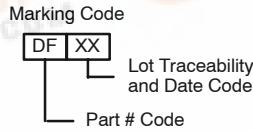
- TrenchFET® Power MOSFETS
- Low r_{DS(on)} Dual and Excellent Power Handling In A Compact Footprint

APPLICATIONS

- Load Switch
- PA Switch
- Battery Switch



Ordering Information: Si5935DC-T1



P-Channel MOSFET P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)				
Parameter	Symbol	5 secs	Steady State	Unit
Drain-Source Voltage	V _{DS}	-20		V
Gate-Source Voltage	V _{GS}	±8		
Continuous Drain Current (T _J = 150°C) ^a	I _D	T _A = 25°C	-4.1	A
		T _A = 85°C	-2.9	
Pulsed Drain Current	I _{DM}	-15		A
Continuous Source Current (Diode Conduction) ^a	I _S	-1.8	-0.9	
Maximum Power Dissipation ^a	P _D	T _A = 25°C	2.1	W
		T _A = 85°C	1.1	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b, c}		260		

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R _{thJA}	t ≤ 5 sec	50	°C/W
		Steady State	90	
Maximum Junction-to-Foot (Drain)	R _{thJF}	30	40	

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Reflow Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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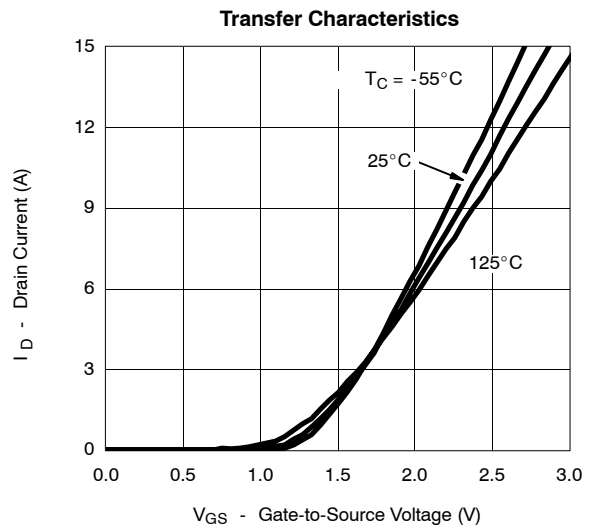
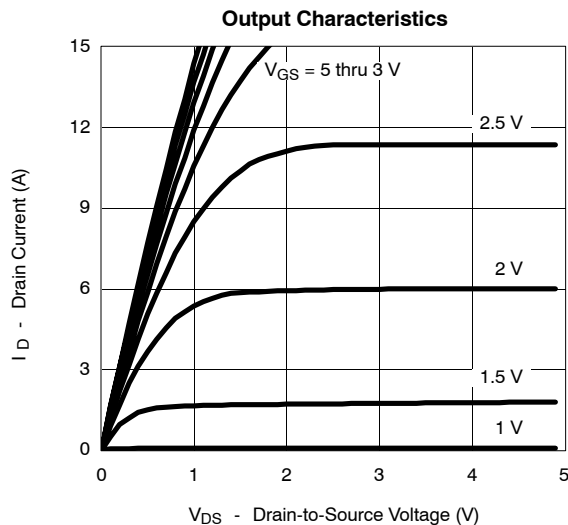


SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-0.4		1.0	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±8 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -16 V, V _{GS} = 0 V			-1	μA
		V _{DS} = -16 V, V _{GS} = 0 V, T _J = 85 °C			-5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ -5 V, V _{GS} = -4.5 V	-15			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = -4.5 V, I _D = -3 A		0.069	0.086	Ω
		V _{GS} = -2.5 V, I _D = -2.5 A		0.097	0.121	
		V _{GS} = -1.8 V, I _D = -0.6 A		0.137	0.171	
Forward Transconductance ^a	g _{fs}	V _{DS} = -10 V, I _D = -3 A		8		S
Diode Forward Voltage ^a	V _{SD}	I _S = -0.9 A, V _{GS} = 0 V		-0.8	-1.2	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = -10 V, V _{GS} = -4.5 V, I _D = -3 A		5.5	8.5	nC
Gate-Source Charge	Q _{gs}			0.91		
Gate-Drain Charge	Q _{gd}			1.6		
Turn-On Delay Time	t _{d(on)}	V _{DD} = -10 V, R _L = 10 Ω I _D ≅ -1 A, V _{GEN} = -4.5 V, R _G = 6 Ω		18	30	ns
Rise Time	t _r			32	50	
Turn-Off Delay Time	t _{d(off)}			42	65	
Fall Time	t _f			26	40	
Source-Drain Reverse Recovery Time	t _{rr}		I _F = -0.9 A, di/dt = 100 A/μs		30	

Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

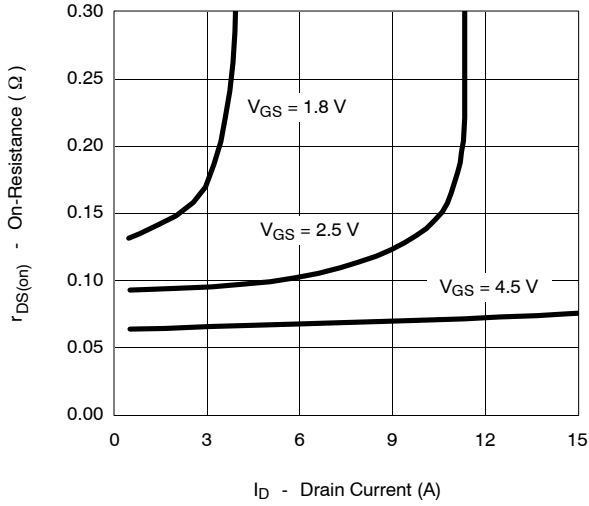
TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



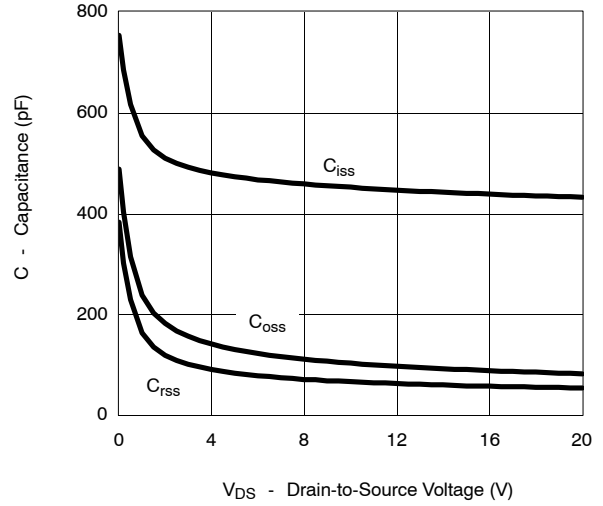


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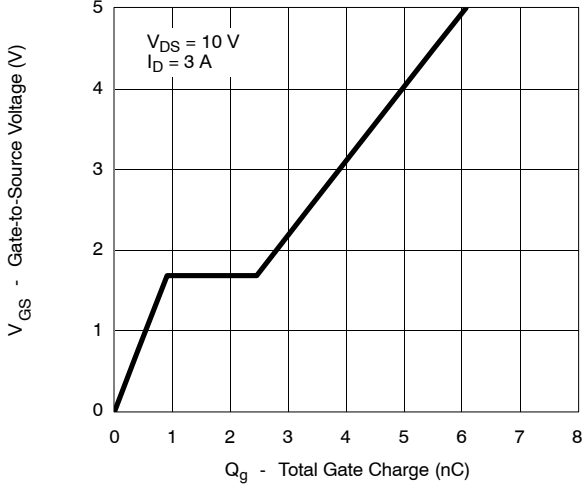
On-Resistance vs. Drain Current



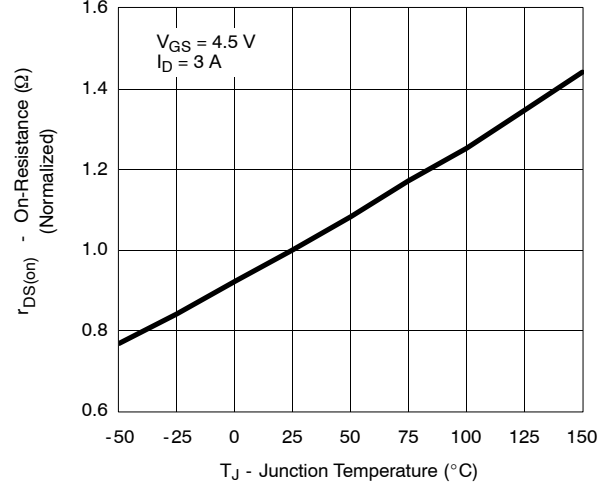
Capacitance



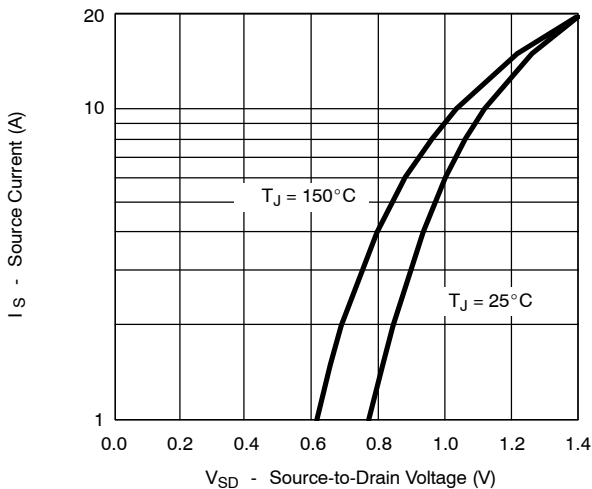
Gate Charge



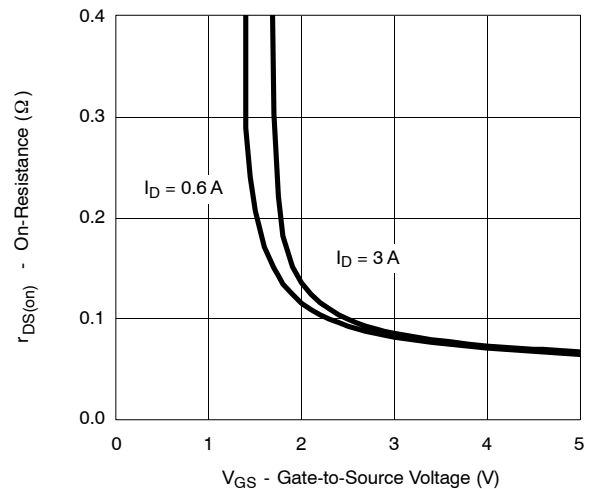
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

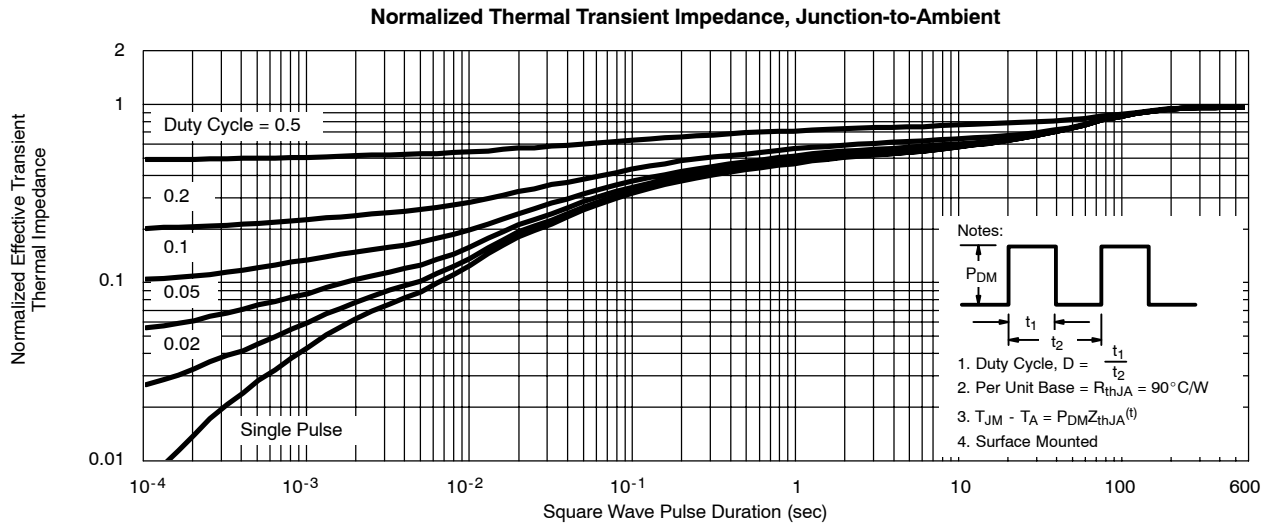
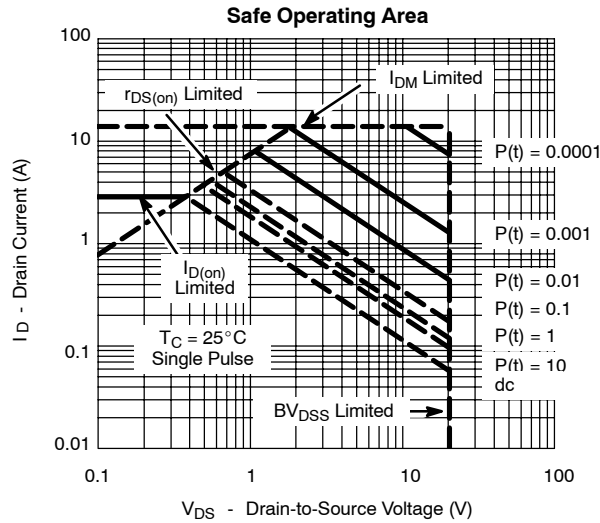
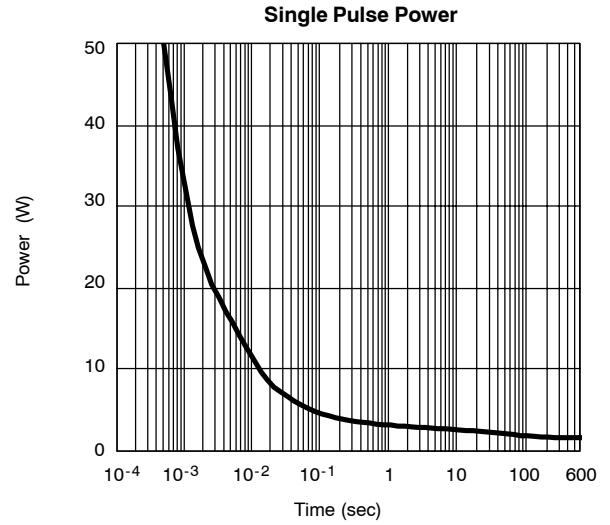
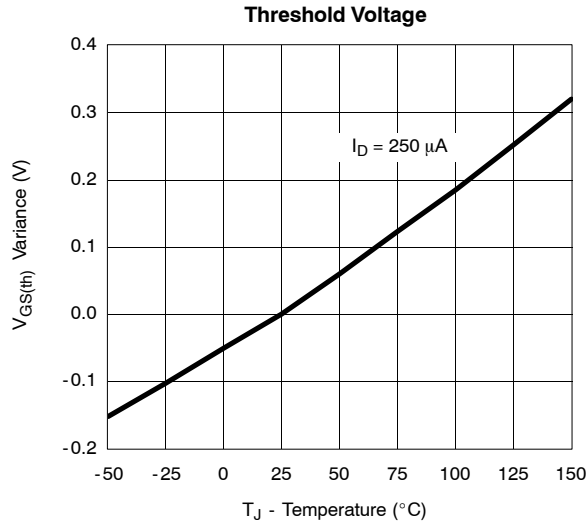


On-Resistance vs. Gate-to-Source Voltage





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